

## SILICON EPITAXIAL PLANAR DIODE

### Band Switching Diode

#### Features

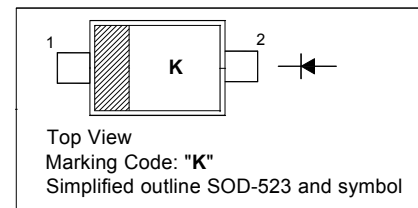
- Extremely small surface mounting type
- High reliability

#### Applications

- High frequency switching

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	35	V
Forward Current	$I_F$	100	mA
Junction Temperature	$T_J$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 125	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	$V_F$	1	V
Reverse Current at $V_R = 25\text{ V}$	$I_R$	10	nA
Capacitance Between Terminals at $V_R = 6\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	1.2	pF
Forward Operating Resistance at $I_F = 2\text{ mA}$ , $f = 100\text{ MHz}$	$r_f$	0.9	$\Omega$

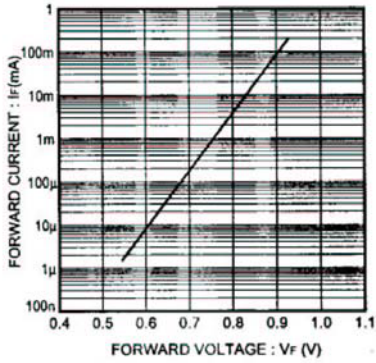


Fig. 1 Forward characteristics

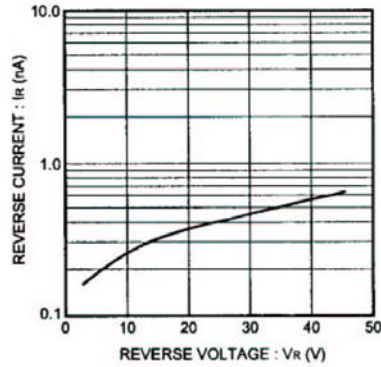


Fig. 2 Reverse characteristics

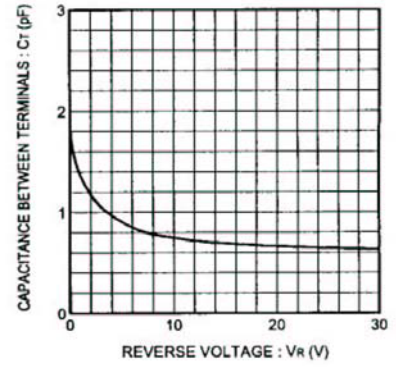


Fig. 3 Capacitance between terminals characteristics

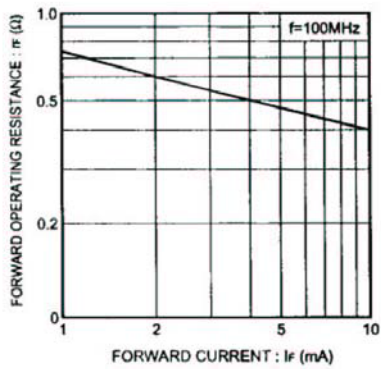


Fig. 4 Forward operating resistance characteristics